

# **ECENCAB5VBH**

**E**core

Low-Capacitance Bidirectional Micro Packaged TVS Diodes for ESD Protection

The ECENCAB5VBH is designed with ECORE Punch-Through process TVS technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium.

This series has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD(electrostatic discharge), and EFT (electrical fast transients).

### Features

- Peak Power Dissipation –65 W (8 x 20 us Waveform)
- Stand-off Voltage: 5.0 V
- Low capacitance for high-speed interfaces
- Replacement for MLV (0402)
- Protects I/O、 VCC Port
- Low Clamping Voltage
- Low Leakage
- Low Capacitance
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- ROHS compliant

## **Main applications**

- Serial and Parallel Ports
- Notebooks, Desktops, Servers
- Projection TV
- Cellular handsets and accessories
- Portable instrumentation
- Peripherals

### **Protection solution to meet**

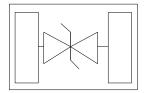
IEC61000-4-2 (ESD) ±20kV (air), ±20kV (contact)

### **Ordering Information**

| Device      | Marking | Qty per Reel | Reel Size |
|-------------|---------|--------------|-----------|
| ECENCAB5VBH | PB      | 10000pcs     | 7inch     |



**DFN1006** 





| Maximum rati   | ngs (Tamb=25°C | Unless C | <b>Otherwise S</b> | necified) |
|----------------|----------------|----------|--------------------|-----------|
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| Maximum ratings (rand-25 C Oness Otherwise Specified) |          |               |       |  |
|---|----------|---------------|-------|--|
| Parameter   | Symbol   | Value         | Unit  |  |
| Peak Pulse Power (tp=8/20µs waveform)                 | Рррр     | 65            | Watts |  |
| Peak pulse current (tp=8/20µs waveform)               | $I_{PP}$ | 6             | А     |  |
| ESD Rating per IEC61000-4-2: Contact                  |          | 20            | KV    |  |
| Air   |          | 20            | ΚV    |  |
| Lead Soldering Temperature                            | TL       | 260 (10 sec.) | °C    |  |
| Operating Temperature Range                           | ΤJ       | -55 ~ 150     | °C    |  |
| Storage Temperature Range                             | Tstg     | -55 ~ 150     | °C    |  |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

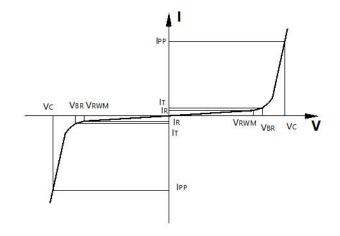
\*Other voltages may be available upon request.

1. Non-repetitive current pulse, per Figure 1.

| Electric | Electrical characteristics (Tamb=25°C Unless Otherwise Specified) |                             |      |      |      |       |
|----------|---|-----------------------------|------|------|------|-------|
| Symbol   | Parameter   | Conditions                  | Min. | Тур. | Max. | Units |
| Vrwm     | Reverse Working Voltage   |                             |      |      | 5    | V     |
| VBR      | Reverse Breakdown Voltage   | $I_T = 1 m A$ ,             | 5.8  |      | 9.5  | V     |
| Ir       | Reverse Leakage Current   | $V_{RWM} = 5V,$             |      |      | 0.5  | μΑ    |
| Vc       | Clamping Voltage  | $I_{PP} = 6A$ , tp =8/20µs, |      | 9    | 12   | V     |
| CJ       | Junction Capacitance  | $V_{R} = 1V, f = 1MHz,$     |      | 13   | 19   | pF    |

Junction capacitance is measured in  $V_R=0V$ ,F=1MHz

| Symbol         | Parameter                          |  |
|----------------|------------------------------------|--|
| Vrwm           | Working Peak Reverse Voltage       |  |
| VBR            | Breakdown Voltage @ I <sub>T</sub> |  |
| Vc             | Clamping Voltage @ IPP             |  |
| I <sub>T</sub> | Test Current                       |  |
| Irm            | Leakage current at VRWM            |  |
| Ірр            | Peak pulse current                 |  |
| Co             | Off-state Capacitance              |  |
| CJ             | Junction Capacitance               |  |





# ECENCAB5VBH

#### Typical electrical characterist applications Waveform Peak Pulse Power-P<sub>PK</sub> (KW) Parameters: tr=8us Ш Percent of IPP td=20us 0.1 Ϊ td=IPP/2 0 0.01 0.1 Pulse Duration-tp (us) Time (us) Non-Repetitive Peak Pulse Power vs. Pulse Time **Pulse Waveform** % of Rated Power or Ipp 10 Ambient Temperature-T A (°C) **Power Derating Curve**



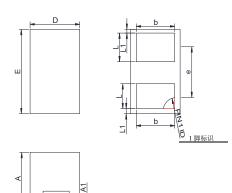
# **Package Information**

### **DFN1006**

# Mechanical Data

Case:DFN1006

Case Material: Molded Plastic. UL Flammability



| DIM | Millimeters |      |  |
|-----|-------------|------|--|
| DIM | Min         | Max  |  |
| Α   | 0.40        | 0.50 |  |
| A1  | 0.00        | 0.05 |  |
| D   | 0.55        | 0.65 |  |
| Е   | 0.95        | 1.05 |  |
| b   | 0.45        | 0.55 |  |
| e   | 0.65TYP     |      |  |
| L   | 0.2         | 0.32 |  |
| L1  | 0.05REF     |      |  |

## **Recommended Pad outline**

